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DECLARATION

As a below named inventor, I/we hereby declare that:

My residence, post office address and citizenship are as stated below next to my name; that

I/we verily believe I am the original and first inventor(s) of the invention entitled: **METHODS FOR FILLING HIGH ASPECT RATIO TRENCHES IN SEMICONDUCTOR LAYERS** (MIO 0109 PA/02-1541), described and claimed

	in the attached specification;
X	_ in the specification filed July 11, 2003, as U.S. Application Serial No.
	10/618.220, and as amended .

I/we hereby authorize the attorney(s) and/or agent(s) appointed herein to indicate above whether the invention is described and claimed in an attached specification and to provide the Filing Date and Serial No. of the corresponding U.S. Application, if previously filed.

I/we hereby state that I/we have reviewed and understand the contents of the above identified specification, including the claims as filed and as amended by any amendment referred to above.

I/we acknowledge the duty to disclose to the Patent and Trademark Office all information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations, §1.56(a).

I/we further declare that all statements made herein of my/our own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under \$1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Full name of sole or first Inventor: Jingyi Bai	
Inventor's signature 1	•
Date: 4/24/03	•
Residence: 3777 Gekeler Lane, Apt. 140 Boise, ID 83706	
Citizenship: P.R. China	
Post Office Address: c/o Micron Technology, Inc. 8000 S. Federal Way Boise, ID 83706-9632	
Full name of second Inventor: Weimin Li	
Inventor's signature	
Date:	
Residence: 5513 E. Quartersawn St. Boise, ID 83716	
Citizenship: China	
Post Office Address: c/o Micron Technology, Inc. 8000 S. Federal Way Boise, ID 83706-9632	
	•
	Inventor's signature Date: 4/24/02 Residence: 3777 Gekeler Lane, Apt. 140 Boise, ID 83706 Citizenship: P.R. China Post Office Address: c/o Micron Technology, Inc. 8000 S. Federal Way Boise, ID 83706-9632 Full name of second Inventor: Weimin Li Inventor's signature Date: Residence: 5513 E. Quartersawn St. Boise, ID 83716 Citizenship: China Post Office Address: c/o Micron Technology, Inc.

Full name of sole or first Inventor: Jingyi Bai Inventor's signature_ Date:_ Residence: 3777 Gekeler Lane, Apt. 140 Boise, ID 83706 Citizenship: P.R. China Post Office Address: c/o Micron Technology, Inc. 8000 S. Federal Way Boise, ID 83706-9632 Full name of second Inventor: Weimin Li Inventor's signature Residence: 5513 E. Quartersawn St. Boise, ID 83716 Citizenship: China Post Office Address: c/o Micron Technology, Inc. 8000 S. Federal Way Boise, ID 83706-9632

Full name of third Inventor: William S. Budge

Inventor's signature_

Date: April 29, 2023

Residence:

404 Cascade Ave.

Homedale, ID 83628

Citizenship: U.S.A.

Post Office Address: c/o Micron Technology, Inc.

8000 S. Federal Way Boise, ID 83706-9632



POWER OF ATTORNEY

Applicants: Jingyi Bai, Weimin Li and William S. Budge Application No.: 10/618,220 Filed: July 11, 2003

Entitled: METHODS FOR FILLING HIGH ASPECT RATIO TRENCHES IN

SEMICONDUCTOR LAYERS

CERTIFICATE UNDER 37 CFR 3.73(b)

Micron Technology, Inc., a corporation of the State of Delaware, with a place of business at 8000 S. Federal Way, Boise, ID 83706-9632 certifies that it is the assignee of the entire right, title and interest in the patent application identified above by virtue of either:

A. [X] An assignment from the inventor(s) of the patent application identified above, a copy of which is attached.

OR

the assignee.

1. From:		To:
The docur	nent was recorde	ed in the Patent and Trademark Office at
Reel	Frame	, or for which a copy thereof is attached.
2. From:		To:
The docum	nent was recorde	ed in the Patent and Trademark Office at
Reel	Frame	, or for which a copy thereof is attached.
3. From:		To:
		ed in the Patent and Trademark Office at
Reel	Frame	, or for which a copy thereof is attached.
[] Addition	onal documents i	n the chain of title are listed on a supplemental sheet.
Copies of assignment	gnments or other	documents in the chain of title are attached.
		the documents in the chain of title of the patent application

The undersigned (whose title is supplied below) is empowered to sign this certificate on behalf of

Micron Technology, Inc. hereby appoints the following attorney(s) and/or agent(s) to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith:

Richard A. Killworth	Reg. No. 26,397
James F. Gottman	Reg. No. 27,262
Timothy W. Hagan	Reg. No. 29,001
James E. Beyer	Reg. No. 39,564
Susan M. Luna	Reg. No. 38,769
Patricia L. Prior	Reg. No. 33,758
William A. Jividen	Reg. No. 42,695
John D. Reed	Reg. No. 46,506
Brian L. Smiler	Reg. No. 46,458
Joan N. Williams	Reg. No. 52,364
Kristina E. Swanson	Reg. No. 53,657
Michael L. Lynch	Reg. No. 30,871
Charles B. Brantley, II.	Reg. No. 38,086

Address all telephone calls to (937) 223-2050. Address all correspondence to: DINSMORE & SHOHL, LLP, One Dayton Centre, One South Main Street, Suite 500, Dayton, Ohio 45402-2023.

Micron Technology, Inc. hereby declares that all statements made herein of my own knowledge are true, and that all statements made on information and belief are believed to be true; and further, that these statements are made with the knowledge that willful false statements, and the like so made, are punishable by fine or imprisonment, or both, under Section 1001, Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Date: November 20, 2003
Name: Michael L. Lynch
Title: Chief Patent Counsel
Signature:

ASSIGNMENT

WHEREAS, we, Jingyi Bai, of Boise, ID; Weimin Li, of Boise, ID, and William S. Budge, of Homedale, ID, invented certain new and useful METHODS FOR FILLING HIGH ASPECT RATIO TRENCHES IN SEMICONDUCTOR LAYERS for which we executed an application for a United States Patent and for which said application for United States Patent was filed on July 11, 2003, under

☑ Patent Application Serial No. 10/618,220

☑ Attorney Docket No. MIO 0109 PA/02-1541;

WHEREAS, we hereby authorize and request the attorney(s) and/or agent(s) empowered to act on our behalf in the aforementioned application, to insert above the filing date and application number of said application, when known;

AND WHEREAS, Micron Technology, Inc., a corporation of the State of Delaware, with a place of business at 8000 S. Federal Way, Boise, Idaho 83706-9632, hereinafter called the Assignee, is desirous of acquiring the entire right, title and interest in and to said application and the inventions therein disclosed and any letters patent that may issue thereon;

NOW, THEREFORE, for good and valuable consideration, receipt whereof is hereby acknowledged, we hereby sell, assign and transfer unto said Assignee, its successors and assigns, the entire right, title and interest in and to said application and any divisions or continuations thereof, and the inventions therein disclosed, and any improvements thereon, and any patent or patents that may be issued or reissued thereon, and we hereby authorize and request the Commissioner of Patents and Trademarks to issue any letters patent thereon, and reissues thereof, to said Assignee, its successors and assigns; and we hereby authorize said Assignee, its successors and assigns, to file in its own name applications for patent in foreign countries in connection with the inventions hereby transferred, under the International Convention claiming the priority of said United States application or otherwise, and to secure in its own name the patent or patents issued thereon; and we hereby agree that, upon request, we will sign all papers, and make all rightful oaths, and do all acts which said Assignee, its successors or assigns, may consider necessary in connection with said United States application, and in connection with any other United States or foreign applications that may be filed in connection with said inventions, and with any improvements thereon, and in connection with any patents issued or reissued thereon.



	Jingyi Bai
State of TDAHO State of TDAHO County of ADA On this 24 day of APLIL the above County and State, personally ar	, 2002 before me a Notary Public in and for ppeared the above named Jingyi Bai personally known
to me, and acknowledged the execution o purpose herein set forth.	of the foregoing assignment as a free act and deed for the

i k

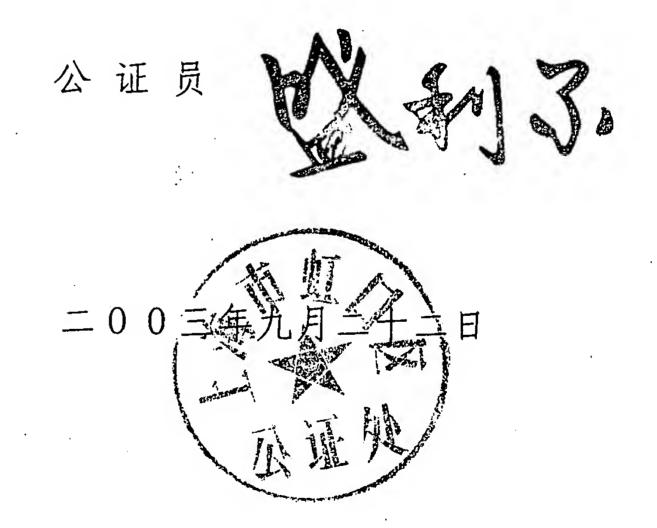
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IN TESTIMONY WH September, 2003.	EREOF, I her	reunto set my hand and seal this 22 day of
		Weimin Li
·		
State of)) ss	
County of)	
the above County and State, personall	y appeared the	_, 2002 before me a Notary Public in and for e above named Weimin Li personally known going assignment as a free act and deed for the
·		Notary Public

公 证 书 (2003) 沪虹证外字第 8403 号

兹证明李卫民(男,一九六九年四月十九日出生,护照号码:147282411)于二00三年九月二十二日来 到我处,在我的面前,在前面的《转让书》上签名。

中华人民共和国上海市虹口区公证处



Translation

NOTARIAL CERTIFICATE

(2003) H.H.Z.W.Z. No. 8403

This is to certify that Weimin Li (male, born on April 19, 1969, Passport No.:147282411) came to this Office and subscribed his name on the foregoing *Assignment* in my presence on September 22, 2003.

SHENG Lier (Seal)

Notary Public

The People's Republic of China

Shanghai Hongkou District Notary Public Office

(Seal)

Dated: September 22, 2003

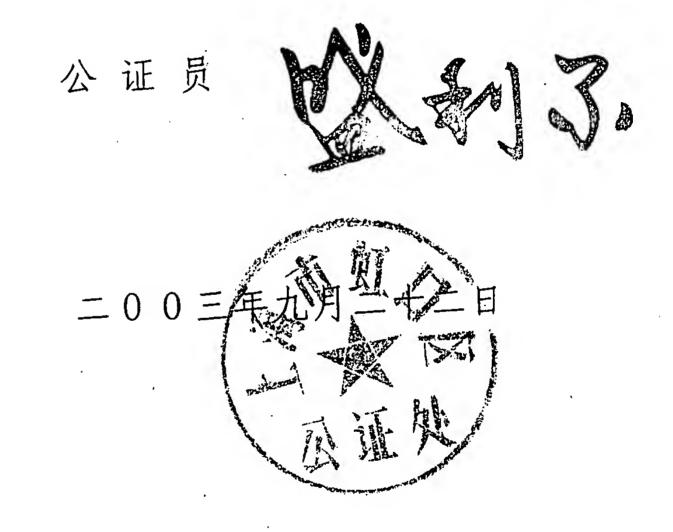


X I 04264517

证 明 书 (2003) 沪虹证外字第 8404 号

兹证明前面的(2003)沪虹证外字第8403号公证书的英文译本内容与该公证书的中文原本相符。

中华人民共和国上海市虹口区公证处



Translation

CERTIFICATE

(2003) H.H.Z.W.Z. No. 8404

This is to certify that the foregoing English version of Notarial Certificate (2003) H.H.Z.W.Z. No. 8403 is true and faithful to the said original Notarial Certificate in Chinese.

SHENG Lier (Seal)

Notary Public

The People's Republic of China

Shanghai Hongkou District Notary Public Office

(Seal)

Dated: September 22, 2003



XI04264516

IN TESTIMONY WHEREOF, I he	ereunto set my hand and seal this <u>Z9</u> day of
	William S. Budge
State of TDAHO) ss County of ADA) ss On this Aday of APRIL the above County and State, personally appeared the known to me, and acknowledged the execution of the purpose herein set forth.	
SKEL ON TARILLAND TARILLAN	Motary Public

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